

**Amendments to the Specification:**

Please replace the paragraph beginning at page 9, line 25, with the following amended paragraph:

In addition, since a light emitting device according to the present invention has a light emitting element using the carbazole derivative according to the present invention, a light emitting device which has the high reliability can be provided.

Please replace the paragraph beginning at page 14, line 8, with the following amended paragraph:

As the aryl group having 6 to 25 carbon atoms, specifically, a phenyl group, 4-biphenyl group, a 1-naphthyl group, a 2-naphthyl group, a 9-anthryl group, a 9-phenanthryl group, a 1-pyrenyl group, a 9,9'-dimethyl-2-fluorenyl group, a spiro-9,9'-bifluorene-2-yl group, and the like can be used. Further, an aryl group having a substituent such as [a] an m-tolyl group, a p-tolyl group, a 2-fluorophenyl group, a 3-fluorophenyl group, and a 4-fluorophenyl group may be used.

Please replace the paragraph beginning at page 14, line 14, with the following amended paragraph:

As the heteroaryl group having 5 to 9 carbon atoms, specifically, a 2-pyridyl group, [a] an 8-quinolyl group, a 3-quinolyl group, and the like can be used.

Please replace the paragraph beginning at page 49, line 8, with the following amended paragraph:

As an electron transporting material forming the electron transporting layer, the metal complexes mentioned above such as Alq<sub>3</sub>, tris(4-methyl-8-quinolinolato)aluminum (abbreviation: Almq<sub>3</sub>), bis(2-methyl-8-quinolinolato)-4-phenylphenolato-aluminum (abbreviation: BAIq), tris(8-quinolinolato)gallium (abbreviation: Gaq<sub>3</sub>), bis(2-methyl-8-quinolinolato)-4-phenylphenolato-gallium (abbreviation: BGaq), bis[10-hydroxybenzo[h]-quinolinolato]beryllium (abbreviation: BeBq<sub>2</sub>), bis[2-(2-hydroxyphenyl)-benzoxazolate]zinc (abbreviation: Zn(BOX)<sub>2</sub>), and bis[2-(2-hydroxyphenyl)-benzothiazolate]zinc (abbreviation: Zn(BTZ)<sub>2</sub>) can be used. Further, 2-(4-biphenyl)-5-(4-tert-butylphenyl)-1,3,4-oxadiazole (abbreviation: PBD), 1,3-bis[5-(p-tert-butylphenyl)-1,3,4-oxadiazole-2-yl]benzene (abbreviation: OXD-7), 3-(4-tert-butylphenyl)-4-(4-ethylphenyl)-5-(4-biphenyl)-1,2,4-triazole (abbreviation: TAZ), 3-(4-tert-butylphenyl)-4-(4-ethylphenyl)-5-(4-biphenyl)-1,2,4-triazole (abbreviation: p-EtTAZ), bathophenanthroline (abbreviation: BPhen), bathocuproin (abbreviation: BCP), and the like can be used in addition to the metal complex.

Please replace the paragraph bridging pages 49 and 50 with the following amended paragraph:

As an electron injecting material for the electron injecting layer, the electron transporting material mentioned above can be used. In addition, an ultrathin film of an insulator, for example, a halogenated alkali metal such as LiF or CsF, a halogenated alkali earth metal such as CaF<sub>2</sub>, an alkali metal oxide such as Li<sub>2</sub>O, or the like is often used. Alkali metal complexes such as lithium acetylacetone (abbreviation: Li(acac)) and 8-quinolinolato-lithium (abbreviation: Liq) are also effective. Furthermore, a layer in which the electron transporting material mentioned above and a metal having a smaller work function such as Mg, Li, and Cs are mixed can be used as the electron injecting layer. In addition, a metal oxide such as molybdenum oxide (MoO<sub>x</sub>), vanadium oxide (VO<sub>x</sub>), ruthenium oxide (RuO<sub>x</sub>), and tungsten oxide (WO<sub>x</sub>), or one of a

benzoxazole derivative and one or more of alkali metal, alkali earth metal, and transition metal may be included. Titanium oxide also may be used.

Please replace the paragraph bridging pages 52 and 53 with the following amended paragraph:

As a material used for the second electrode (cathode) 617 formed on the layer containing the light emitting material 616, it is preferable to use a material having a smaller work function (Al, Mg, Li, Ca, an alloy or a compound thereof such as MgAg, MgIn, AlLi, CaF<sub>2</sub>, LiF, and calcium nitride). When light which is generated in the layer containing the light emitting material 616 is transmitted through the second electrode 617, a lamination layer of a metal thin film with a thinned thickness and a transparent conductive film (ITO, indium oxide containing [[zinic]] zinc oxide of 2 % to 20 %, indium tin oxide containing silicon, [[zinic]] zinc oxide (ZnO), and the like) may be used as the second electrode (cathode) 617.

Please replace the paragraph bridging pages 57 and 58 with the following amended paragraph:

627.64 mg (1.7 mmol) of 3-iodine-9-phenylcarbazole, 672.86 mg (2.0 mmol) of N-(4-diphenylaminophenyl)-N-phenylamine, 57.5 mg (0.1 mmol) of dibenzylideneacetonepalladium, and 335 mg (3.5 mmol) of sodium tert-butoxide were put into a three-necked flask, and the atmosphere in the flask was replaced by nitrogen. 3.5 ml of dehydrated toluene was added thereto and degassing was carried out for 3 minutes. After adding 0.4 ml of tri-tert-butylphosphine (10 w% hexane solution), the flask was shaked lightly up and down to stir the content. The solution was heated and stirred at 80 °C for 10 minutes with irradiating by a microwave at 200 W. After the reaction, saturated aqueous solution of sodium chloride was added, and the extraction

with 100 ml of ethyl acetate was carried out. Further, magnesium sulfate was added to remove moisture, and then, magnesium sulfate was removed by filtration. Filtrate was condensed and purified by silica gel column using a solution of ethyl acetate and hexane in a ratio of 1:1. Hexane was added to the purified solution, and recrystallization was carried out to obtain 650 mg of cream powder in a yield of 65 %. The NMR data are indicated below.  $^1\text{H}$  NMR (300MHz, DMSO-d);  $\delta$ =6.89-7.05 (m, 13H), 7.21-7.28 (m, 9H), 7.32-7.43 (m, 3H), 7.50-7.69 (m, 5H), 8.02(s, 1H), 8.14 (d,  $J$ =7.2, 1 H). In addition, FIG. 13 shows a chart of  $^1\text{H}$  NMR, and FIG. 14 shows an enlarged view of the portion of 6.0 to 9.0 ppm in FIG. 13.

Please replace the paragraph beginning at page 62, line 26, with the following amended paragraph:

A first electrode 201 of the light emitting element [[is]] was formed over a substrate 200. In this example, the first electrode functions as an anode. The anode [[is]] was formed by a sputtering method using indium tin oxide containing silicon oxide which is a material for a transparent conductive film to have a thickness of 110 nm.

Please replace the paragraph bridging pages 62 and 63 with the following amended paragraph:

Then, a layer containing a light emitting material 202 [[is]] was formed over the first electrode 201. In this example, the layer containing the light emitting material 202 [[is]] was formed by stacking a hole injecting layer 204, a hole transporting layer 211, a light emitting layer 212, an electron transporting layer 213, and an electron injecting layer 214.

Please replace the paragraph beginning on page 63, line 5, with the following amended paragraph:

The substrate provided with the first electrode 201 [[is]] was fixed in a substrate holder in a commercially available vacuum vapor deposition equipment so that the surface provided with the first electrode 201 faces downward. The carbazole derivative according to the present invention [[is]] was provided to a deposition source in the vacuum vapor deposition equipment to form the hole injecting layer 204 by a vapor deposition method with a resistance heating method to have a thickness of 50 nm. As a material for forming the hole injecting layer 204, PCzDPA1 represented by the structural formula (28) [[is]] was used in this example.

Please replace the paragraph beginning at page 63, line 13, with the following amended paragraph:

Then, the hole transporting layer 211 [[is]] was formed with a material which is excellent in a hole transporting property. As a material for the hole transporting layer 211, a known hole transporting material can be used. In this example, the hole transporting layer 211 [[is]] was formed by the same method as that of the hole injecting layer 204 using  $\alpha$ -NPD to have a thickness of 10 nm.

Please replace the paragraph beginning at page 63, line 18, with the following amended paragraph:

The light emitting layer 212 [[is]] was formed. In the light emitting layer 212, holes and electrons recombine with each other and emit light. In this example, a host material of Alq<sub>3</sub> and a guest material of coumarin 6 [[are]] were co-evaporated to form

the light emitting layer 212 to have a thickness of 40 nm including coumarin 6 in Alq<sub>3</sub> at 1 wt%.

Please replace the paragraph beginning at page 63, line 22, with the following amended paragraph:

The electron transporting layer 213 [[is]] was formed. As a material for the electron transporting layer 213, a known electron transporting material can be used. In this example, the electron transporting layer [[is]] was formed by a vapor deposition method using Alq<sub>3</sub> to have a thickness of 30 nm.

Please replace the paragraph beginning at page 63, line 26, with the following amended paragraph:

Thereafter, the electron injecting layer 214 [[is]] was formed. As the electron injecting layer 214, a known electron injecting material can be used. In this example, the electron injecting layer [[is]] was formed by a vapor deposition method using calcium fluoride to have a thickness of 1 nm.

Please replace the paragraph bridging pages 63 and 64, with the following amended paragraph:

After the layer containing the light emitting material 202 [[is]] was formed by stacking the hole injecting layer 204, the hole transporting layer 211, the light emitting layer 212, the electron transporting layer 213, and the electron injecting layer 214, a second electrode 203 [[is]] was formed by a sputtering method or a vapor deposition method. In this example, the second electrode functions as a cathode. In this example,

the second electrode [[is]] was formed by a vapor deposition method using Al to have a thickness of 200 nm.

Please replace the paragraph beginning on page 64, line 7, with the following amended paragraph:

Thus, a light emitting element of this example [[is]] was formed.

Please replace the paragraph beginning on page 64, line 15, with the following amended paragraph:

Like Example 3, an anode [[is]] was formed by indium tin oxide containing silicon oxide to have a thickness of 110 nm, a hole injecting layer [[is]] was formed by a carbazole derivative PCzDPA2 according to the present invention represented by the structural formula (56) to have a thickness of 50 nm, a hole transporting layer [[is]] was formed by  $\alpha$ -NPD to have a thickness of 10 nm, and a light emitting layer [[is]] was formed by Alq<sub>3</sub> and coumarin 6 to have a thickness of 40 nm including coumarin 6 in Alq<sub>3</sub> at 1 wt% over a substrate. Then, an electron transporting layer [[is]] was formed by Alq<sub>3</sub> to have a thickness of 30 nm, an electron injecting layer [[is]] was formed by calcium fluoride to have a thickness of 1 nm, and a cathode [[is]] was formed by Al to have a thickness of 200 nm.

Please replace the paragraph beginning at page 64, line 24, with the following amended paragraph:

Thus, a light emitting element of this example [[is]] was formed.

Please replace the paragraph beginning at page 64, line 26, with the following amended paragraph:

As a comparative example, a light emitting element [[is]] was formed using 4,4'-bis(N-{4-[N,N-bis(3-methylphenyl)amino]phenyl}-N-phenylamino)biphenyl (abbreviation: DNTPD) for a hole injecting layer.

Please replace the paragraph bridging pages 64 and 65, with the following amended paragraph:

Like Example 3, an anode [[is]] was formed by indium tin oxide containing silicon oxide to have a thickness of 110 nm, a hole injecting layer [[is]] was formed by DNTPD to have a thickness of 50 nm, a hole transporting layer [[is]] was formed by  $\alpha$ -NPD to have a thickness of 10 nm, and a light emitting layer [[is]] was formed by Alq<sub>3</sub> and coumarin 6 to have a thickness of 40 nm including coumarin 6 in Alq<sub>3</sub> at 1 wt% over a substrate. Then, an electron transporting layer [[is]] was formed by Alq<sub>3</sub> to have a thickness of 30 nm, an electron injecting layer [[is]] was formed by calcium fluoride to have a thickness of 1 nm, and a cathode [[is]] was formed by Al to have a thickness of 200 nm.

Please replace the paragraph beginning at page 65, line 22, with the following amended paragraph:

FIG. 9 shows changes in standardized luminance over time and FIG. 10 shows changes in voltage over time of the light emitting elements manufactured in Example 3 and Comparative Example 1. As a measuring method, the initial luminance [[is]] was set at 3000 cd/m<sup>2</sup> and the change in the luminance over time and the change in the voltage over time [[are]] were measured while a constant current being supplied.

Please replace the paragraph bridging pages 65 and 66, with the following amended paragraph:

According to FIG. 9, the luminance of the light emitting element manufactured in Example 3 [[is]] was not reduced over time as much as that of the light emitting element manufactured in Comparative Example 1. Further, according to FIG. 10, in the light emitting element manufactured in Example 3, the voltage hardly increases increased over time. Therefore, the light emitting element having the carbazole derivative according to the present invention has a long life time and improved reliability.

Please replace the paragraph beginning on page 66, line 3, with the following amended paragraph:

As shown in Example 1 and Example 2, HOMO level of PCzDPA1 represented by the structural formula (28) [[is]] was -5.16 eV and HOMO level of PCzDPA2 represented by the structural formula (56) [[is]] was -5.16 eV. On the other hand, HOMO level of DNTPD shown in Comparative Example [[is]] was -5.15 eV which [[is]] was approximately same as that of PCzDPA1 and PCzDPA2 as measured by the same method. Consequently, the carbazole derivative according to the present invention has an approximately same hole injecting property as that of DNTPD. Therefore, a hole injection barrier against the anode can be reduced, and so the driving voltage can be reduced.

Please replace the paragraph beginning on page 70, line 5, with the following amended paragraph:

A flask was charged with 3.2 g (10 mmol) of 4-bromotriphenylamine, 1.4 g (10 mmol) of 1-aminonaphthalene, 58 mg (0.1mmol) of dibenzylideneacetonepalladium(0),

and 3.0 g (30 mmol) of sodium tert-butoxide and the atmosphere in the flask was replaced by nitrogen. 40 ml of dehydrated xylene was added thereto. Degassing was carried out for approximately 3 minutes until no more air bubbles were generated. 540 mg (1.0 mmol) of 1,1-bis(diphenylphosphino)ferrocene [*[(i)s]*] was added thereto and the solution was stirred for 6.5 hours at 90° C in an atmosphere of nitrogen. After approximately 300 ml of toluene was added thereto, the solution was filtered through florisil, alumina, and celite. The obtained filtrate was washed with water and a saturated aqueous solution of sodium chloride. The organic layer was dried by magnesium sulfate. The obtained material was filtered, then, condensed, and then, purified by silica gel column chromatography (toluene and hexane in a ratio of 3:7). The obtained solution was condensed, then, hexane was added thereto and the object was precipitated by using an ultra sonic washing machine. The obtained solid was filtered to obtain 1.8 g of N-(4-diphenylaminophenyl)-N-(1-naphthyl)amine as white powder in a yield of 46%. The NMR data of the object are indicated below.  $^1\text{H}$  NMR (300MHz, DMSO-d);  $\delta$ =6.93-7.00 (m, 8H), 7.09 (d,  $j$ =8.7, 2H), 7.23-7.32 (m, 5H), 7.39 (t,  $j$ =7.8, 1H), 7.48-7.52 (m, 3H), 7.86-7.90 (m, 1H), 8.20-8.23 (m, 2H).  $^{13}\text{C}$  NMR (60 MHz, DMSO-d);  $\delta$ =113.2, 118.6, 120.9, 121.7, 122.2, 122.6, 125.0, 126.0, 126.2, 126.6, 127.0, 128.1, 129.3, 134.4, 139.1, 139.6, 141.4, 147.6. FIG. 21 shows a chart of  $^1\text{H}$  NMR and FIG. 22 shows an enlarged view of the portion from 6.5 to 8.5 ppm in FIG. 21. FIG. 23 shows a chart of  $^{13}\text{C}$  NMR.

Please replace the paragraph bridging pages 71 and 72, with the following amended paragraph:

A flask was charged with 740 mg (2.0 mmol) of 3-iodo-9-phenylcarbazole, 700 mg (1.8 mmol) of N-(4-diphenylaminophenyl)-N-(1-naphthyl)amine, 12 mg (0.02 mmol) of dibenzylideneacetonepalladium, and 600 mg (6.0 mmol) of sodium tert-butoxide and the atmosphere in the flask was replaced by nitrogen. 5 ml of dehydrated xylene was

added thereto and degassing was carried out for 3 minutes. After 0.1ml (0.05 mmol) of tri-tert-butylphosphine (10 w% hexane solution) was added thereto, the solution was stirred for 5.5 hours at 90 °C in an atmosphere of nitrogen. Toluene of approximately 100 ml was added thereto and the solution [[is]] was filtered through florisil, alumina, and celite. The obtained filtrate was washed with water and a saturated aqueous solution of sodium chloride. The organic layer was dried by magnesium sulfate. The obtained material was filtered, and condensed, then, purified by silica gel column chromatography (toluene and hexane in a ratio of 3:7). The obtained solution was condensed. Then, hexane was added thereto and the object was precipitated by using an ultra sonic washing machine. The obtained solid was filtered to obtain 500 mg of PCzTPN1 as yellow powder in a yield of 44 %. The NMR data of the object are indicated below.  $^1\text{H}$  NMR (300MHz, DMSO-d);  $\delta$ = 6.74 (d,  $j=8.7$ , 2H), 6.88-7.00 (m, 8H), 7.16-7.67 (m, 23H), 7.84 (d,  $j=8.4$ , 1H), 7.97 (d,  $j=8.1$ , 1H), 8.02 (s, 1H), 8.08 ( $t$ ,  $j=7.8$ , 2H). FIG. 24 shows chart of  $^1\text{H}$  NMR and FIG. 25 shows an enlarged view of the portion from 6.0 to 8.5 ppm in FIG. 24.

Please replace the paragraph beginning on page 77, line 21, with the following amended paragraph:

A first electrode 301 of the light emitting element [[is]] was formed over a substrate 300. In this example, the first electrode functions as an anode. The anode [[is]] was formed by a sputtering method using indium tin oxide containing silicon oxide which is a material for a transparent conductive film to have a thickness of 110 nm.

Please replace the paragraph beginning on page 77, line 25, with the following amended paragraph:

Then, a layer containing a light emitting material 302 [[is]] was formed over the first electrode 301. In this example, the layer containing the light emitting material 302 [[is]] was formed by stacking a hole injecting layer 311, a hole transporting layer 312, a light emitting layer 313, an electron transporting layer 314, and an electron injecting layer 315.

Please replace the paragraph bridging pages 77 and 78, with the following amended paragraph:

The substrate provided with the first electrode 301 [[is]] was fixed in a substrate holder in a commercially available vacuum vapor deposition equipment so that the surface provided with the first electrode 301 faces downward. DNTPD [[is]] was provided to a deposition source in the vacuum vapor deposition equipment to form the hole injecting layer 311 by a vapor deposition method with a resistance heating method to have a thickness of 50 nm.

Please replace the paragraph beginning at page 78, line 6, with the following amended paragraph:

Then, the hole transporting layer 312 [[is]] was formed with a material which is excellent in a hole transporting property. In this example, the hole transporting layer 211 [[is]] was formed by the same method as that of the hole injecting layer using PCzDPA1 represented by the structural formula (28) to have a thickness of 10 nm.

Please replace the paragraph beginning at page 78, line 10, with the following amended paragraph:

The light emitting layer 313 [[is]] was formed. In the light emitting layer 313, holes and electrons recombine with each other and emit light. In this example, a host material of Alq<sub>3</sub> and a guest material of coumarin 6 [[are]] were co-evaporated to form the light emitting layer 313 to have a thickness of 40 nm so that the weight ratio can be 1:0.08 (=Alq<sub>3</sub>:coumarin 6). Thereby coumarin 6 [[is]] was dispersed in the layer made of Alq<sub>3</sub>.

Please replace the paragraph beginning at page 78, line 15, with the following amended paragraph:

The electron transporting layer 314 [[is]] was formed. As a material for the electron transporting layer 314, various kinds of electron transporting materials can be used. In this example, the electron transporting layer [[is]] was formed by a vapor deposition method using Alq<sub>3</sub> to have a thickness of 30 nm.

Please replace the paragraph beginning at page 78, line 19, with the following amended paragraph:

Thereafter, the electron injecting layer 315 [[is]] was formed. As the electron injecting layer 315, various kinds of electron injecting materials can be used. In this example, the electron injecting layer [[is]] was formed by a vapor deposition method using calcium fluoride to have a thickness of 1 nm.

Please replace the paragraph beginning at page 78, line 23, with the following amended paragraph:

After the layer containing the light emitting material 302 [[is]] was formed by stacking the hole injecting layer 311, the hole transporting layer 312, the light emitting

layer 313, the electron transporting layer 314, and the electron injecting layer 315, a second electrode 303 [[is]] was formed by a sputtering method or a vapor deposition method. In this example, the second electrode functions as a cathode. In this example, the cathode [[is]] was formed by a vapor deposition method using Al to have a thickness of 200 nm.

Please replace the paragraph beginning at page 78, line 29, with the following amended paragraph:

Thus, a light emitting element of this example [[is]] was formed.

Please replace the paragraph beginning at page 79, line 3, with the following amended paragraph:

Like Example 9, an anode [[is]] was formed using indium tin oxide containing silicon oxide to have a thickness of 110 nm, a hole injecting layer [[is]] was formed using DNTPD to have a thickness of 50 nm, a hole transporting layer [[is]] was formed using the carbazole derivative PCzDPA2 according to the present invention represented by the structural formula (56) to have a thickness of 50 nm, a light emitting layer [[is]] was formed using Alq<sub>3</sub> and coumarin 6 so that the weight ratio can be 1:0.08 (=Alq<sub>3</sub>:coumarin 6) to have a thickness of 40 nm over a substrate. Then, an electron transporting layer [[is]] was formed using Alq<sub>3</sub> to have a thickness of 30 nm, an electron injecting layer [[is]] was formed using calcium fluoride to have a thickness of 1 nm, and a cathode [[is]] was formed using Al to have a thickness of 200 nm.

Please replace the paragraph beginning at page 79, line 13, with the following amended paragraph:

Thus, a light emitting element of this example [[is]] was formed.

Please replace the paragraph beginning at page 79, line 14, with the following amended paragraph:

FIG. 31 shows luminance-voltage characteristics and FIG. 32 shows current efficiency-luminance characteristics of the light emitting elements manufactured in Example 11 and Example 12. FIG. 33 shows emission spectra of the light emitting elements manufactured in Example 11 and Example 12 when 1 mA of current [[is]] was supplied.

Please replace the paragraph beginning at page 79, line 19, with the following amended paragraph:

According to FIGs. 31 and 32, the carbazole derivative according to the present invention [[is]] was excellent in the hole transporting property and can be used for a hole transporting layer of a light emitting element. Specifically, in the case of the light emitting element manufactured in Example 11, voltage required for light emission at luminance of 1054 cd/m<sup>2</sup> was 8.2 V and a current at this time was 0.82 mA (an electric current density was 20.5 mA/cm<sup>2</sup>). Current efficiency was 5.15 mA/cm<sup>2</sup> and the chromaticity coordinates were (x, y) = (0.30, 0.64). Similarly, in the case of the light emitting element manufactured in Example 12, a voltage required for luminance of 963 cd/m<sup>2</sup> was 8.4 V and a current at this time was 0.80 mA (an electric current density was 19.9 mA/cm<sup>2</sup>). Current efficiency was 4.8 mA/cm<sup>2</sup> and the chromaticity coordinates were (x, y) = (0.30, 0.64).

Please replace the paragraph beginning at page 80, line 10, with the following amended paragraph:

A first electrode 401 of the light emitting element [[is]] was formed over a substrate 400. In this example, the first electrode functions as an anode. The anode [[is]] was formed by a sputtering method using indium tin oxide containing silicon oxide which is a material for a transparent conductive film to have a thickness of 110 nm.

Please replace the paragraph beginning at page 80, line 14, with the following amended paragraph:

Then, a layer containing a light emitting material 402 [[is]] was formed over the first electrode 401. In this example, the layer containing the light emitting material 402 [[is]] was formed by stacking a hole injecting layer 411, a hole transporting layer 412, a light emitting layer 413, an electron transporting layer 414, and an electron injecting layer 415.

Please replace the paragraph beginning at page 80, line 19, with the following amended paragraph:

The substrate provided with the first electrode 401 [[is]] was fixed in a substrate holder in a commercially available vacuum vapor deposition equipment so that the surface provided with the first electrode 401 faces downward. DNTPD [[is]] was provided to a deposition source in the vacuum vapor deposition equipment to form the hole injecting layer 411 by a vapor deposition method with a resistance heating method to have a thickness of 50 nm.

Please replace the paragraph beginning at page 80, line 25, with the following amended paragraph:

Then, the hole transporting layer 412 [[is]] was formed with a material which is excellent in a hole transporting property. As a material for the hole transporting layer 412, various kinds of hole transporting materials can be used. In this example, the hole transporting layer 412 [[is]] was formed by the same method as that of the hole injecting layer using  $\alpha$ -NPD to have a thickness of 30 nm.

Please replace the paragraph bridging pages 80 and 81, with the following amended paragraph:

The light emitting layer 413 [[is]] was formed. In the light emitting layer 413, holes and electrons recombine with each other and emit light. In this example, a host material of 2-tert-butyl-9,10-di(2-naphthyl)anthracene (abbreviation: t-BuDNA) and a guest material of PCzDPA2 represented by the structural formula (56) [[are]] were co-evaporated to form the light emitting layer 413 having a thickness of 40 nm so that the weight ratio can be 1:0.05 (=t-BuDNA:PCzDPA2). Thereby PCzDPA2 [[is]] was dispersed in the layer made of t-BuDNA.

Please replace the paragraph beginning at page 81, line 7, with the following amended paragraph:

The electron transporting layer 414 [[is]] was formed. As a material for the electron transporting layer 414, various kinds of electron transporting materials can be used. In this example, the electron transporting layer [[is]] was formed by a vapor deposition method using Alq<sub>3</sub> to have a thickness of 30 nm.

Please replace the paragraph beginning at page 81, line 11, with the following amended paragraph:

Thereafter, the electron injecting layer 415 [[is]] was formed. As the electron injecting layer 415, various kinds of electron injecting materials can be used. In this example, the electron injecting layer [[is]] was formed by a vapor deposition method using calcium fluoride to have a thickness of 1 nm.

Please replace the paragraph beginning at page 81, line 15, with the following amended paragraph:

After the layer containing the light emitting material 402 [[is]] was formed by stacking the hole injecting layer 411, the hole transporting layer 412, the light emitting layer 413, the electron transporting layer 414, and the electron injecting layer 415, a second electrode 403 [[is]] was formed by a sputtering method or a vapor deposition method. In this example, the second electrode functions as a cathode. In this example, the cathode [[is]] was formed by a vapor deposition method using Al to have a thickness of 200 nm.

Please replace the paragraph beginning at page 81, line 21, with the following amended paragraph:

Thus, a light emitting element of this example [[is]] was formed.

Please replace the paragraph beginning at page 81, line 22, with the following amended paragraph:

FIG. 35 shows a luminance-voltage characteristic and FIG. 36 shows a current efficiency-luminance characteristic of the light emitting element manufactured in Example 13. FIG. 37 shows an emission spectrum of the light emitting element manufactured in Example 13 when 1 mA of current [[is]] was supplied.

Please replace the paragraph beginning at page 82, line 10, with the following amended paragraph:

A first electrode 401 of the light emitting element [[is]] was formed over a substrate 400. In this example, the first electrode functions as an anode. The anode [[is]] was formed by a sputtering method using indium tin oxide containing silicon oxide which [[is]] was a material for a transparent conductive film to have a thickness of 110 nm.

Please replace the paragraph beginning at page 82, line 14, with the following amended paragraph:

Then, a layer containing a light emitting material 402 [[is]] was formed over the first electrode 401. In this example, the layer containing the light emitting material 402 [[is]] was formed by stacking a hole injecting layer 411, a hole transporting layer 412, a light emitting layer 413, an electron transporting layer 414, and an electron injecting layer 415.

Please replace the paragraph beginning at page 82, line 19, with the following amended paragraph:

The substrate provided with the first electrode 401 [[is]] was fixed in a substrate holder in a commercially available vacuum vapor deposition equipment so that the surface provided with the first electrode 401 faces downward. DNTPD [[is]] was provided to a deposition source in the vacuum vapor deposition equipment to form the hole injecting layer 411 by a vapor deposition method with a resistance heating method to have a thickness of 50 nm.

Please replace the paragraph beginning at page 82, line 25, with the following amended paragraph:

Then, the hole transporting layer 412 [[is]] was formed with a material which is excellent in a hole transporting property. As a material for the hole transporting layer 412, various kinds of hole transporting materials can be used. In this example, the hole transporting layer 412 [[is]] was formed by the same method as that of the hole injecting layer using 2,2',7,7'-tetra(diphenylamino)-spiro-9,9'-bifluorene (abbreviation: spiro-TAD) to have a thickness of 30 nm.

Please replace the paragraph beginning at page 83, line 1, with the following amended paragraph:

The light emitting layer 413 [[is]] was formed. In the light emitting layer 413, holes and electrons recombine with each other and emit light. In this example, a host material of 2-tert-butyl-9,10-di(2-naphthyl)anthracene (abbreviation: t-BuDNA) and a guest material of PCzDPA2 represented by the structural formula (56) [[are]] were co-evaporated to form the light emitting layer 413 having a thickness of 40 nm so that the weight ratio can be 1:0.05 (=t-BuDNA:PCzDPA2). Thereby PCzDPA2 [[is]] was dispersed in the layer made of t-BuDNA.

Please replace the paragraph beginning at page 83, line 8, with the following amended paragraph:

The electron transporting layer 414 [[is]] was formed. As a material for the electron transporting layer 414, various kinds of electron transporting materials can be

used. In this example, the electron transporting layer [[is]] was formed by a vapor deposition method using Alq<sub>3</sub> to have a thickness of 30 nm.

Please replace the paragraph beginning on page 83, line 12, with the following amended paragraph:

Thereafter, the electron injecting layer 415 [[is]] was formed. As the electron injecting layer 415, various kinds of electron injecting materials can be used. In this example, the electron injecting layer [[is]] was formed by a vapor deposition method using calcium fluoride to have a thickness of 1 nm.

Please replace the paragraph beginning at page 83, line 16, with the following amended paragraph:

After the layer containing the light emitting material 402 [[is]] was formed by stacking the hole injecting layer 411, the hole transporting layer 412, the light emitting layer 413, the electron transporting layer 414, and the electron injecting layer 415, a second electrode 403 [[is]] was formed by a sputtering method or a vapor deposition method. In this example, the second electrode functions as a cathode. In this example, the cathode [[is]] was formed by a vapor deposition method using Al to have a thickness of 200 nm.

Please replace the paragraph beginning at page 83, line 22, with the following amended paragraph:

Thus, a light emitting element of this example [[is]] was formed.

Please replace the paragraph beginning at page 83, line 23, with the following amended paragraph:

FIG. 38 shows a luminance-voltage characteristic and FIG. 39 shows a current efficiency-luminance characteristic of the light emitting element manufactured in Example 14. FIG. 40 shows an emission spectrum of the light emitting element manufactured in Example 14 when 1 mA of current [[is]] was supplied.